

IN THE CLAIMS

1. **(original)** A method of forming a semiconductor thin-film, comprising:

 irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region;

and

 irradiating a second laser beam to the thin-film in such a way as not to overlap with the
first irradiated region, thereby forming a second irradiated region and a non-irradiated region;

 wherein the second laser beam is irradiated to the thin-film to be coaxial with the first
laser beam;

 and wherein an alignment mark is formed by using an optical constant difference
between the second irradiated region and the non-irradiated region.
2. **(original)** The method according to claim 1, wherein the second laser beam is controlled
in such a way that the second irradiated region is solid.
3. **(currently amended)** The ~~met~~ method according to claim 1, wherein the second laser
beam is controlled in such a way that the second irradiated region is hollow due to ablation.
4. **(original)** The method according to claim 1, wherein the first irradiated region serves as
an annealed semiconductor region, in which an active region of a TFT is formed.
5. **(original)** The method according to claim 1, wherein the semiconductor thin-film is made
of a-Si (amorphous silicon).

6. **(original)** The method according to claim 1, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

7. **(original)** The method according to claim 1, wherein an excimer laser is used to generate the first laser beam.

8. **(original)** A method of forming a semiconductor thin-film, comprising:
irradiating a first laser beam to a semiconductor thin-film to form a first irradiated region;
and
irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;
wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;
and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region or between the second irradiated region and a remaining non-irradiated region of the thin-film.

9. **(original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

10. **(original)** The method according to claim 8, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

11. **(original)** The method according to claim 8, wherein the first irradiated region serves as a annealed semiconductor region, in which an active region of a TFT is formed.
12. **(original)** The method according to claim 8, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).
13. **(original)** The method according to claim 8, wherein the semiconductor thin-film is made of poly-Si film (polysilicon).
14. **(original)** The method according to claim 8, wherein an excimer laser is used to generate the first laser beam.
15. **(currently amended)** A [[The]] method of forming a semiconductor thin-film, comprising:
 - irradiating a first laser beam to a whole semiconductor thin-film to form a first irradiated region; and
 - irradiating a second laser beam to the thin-film in such a way as to overlap with the first irradiated region, thereby forming a second irradiated region;
 - wherein the second laser beam is irradiated to the thin-film to be coaxial with the first laser beam;
 - and wherein an alignment mark is formed by using an optical constant difference between the first irradiated region and the second irradiated region.

16. **(original)** The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is solid.

17. **(original)** The method according to claim 15, wherein the second laser beam is controlled in such a way that the second irradiated region is hollow due to ablation.

18. **(original)** The method according to claim 15, wherein the first irradiated region serves as an annealed semiconductor region, in which an active region of a TFT is formed.

19. **(original)** The method according to claim 15, wherein the semiconductor thin-film is made of a-Si (amorphous silicon).

20. **(original)** The method according to claim 15, wherein the semiconductor thin-film is made of poly-Si (polysilicon).

21. **(original)** The method according to claim 15, wherein an excimer laser is used to generate the first laser beam.

22-26. **(canceled)**